

Silicon Switching Diode Array

- Bridge configuration
- High-speed switching diode chip
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BGX50A



Туре	Package	Configuration	Marking
BGX50A	SOT143	bridge	U1s

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	50	V	
Peak reverse voltage	V _{RM}	70		
Forward current	IF .	140	mA	
Non-repetitive peak surge forward current	/ _{FSM}	-		
Total power dissipation	P _{tot}	210	mW	
$T_{\rm S} \le 74^{\circ}{\rm C}$				
Junction temperature	T _j	150	°C	
Storage temperature	T _{stq}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	360	K/W
BGX50A			

¹Pb-containing package may be available upon special request

 $^2 \rm For}$ calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	1				
Breakdown voltage	V _(BR)	-	-	-	
Reverse current	I _R				μA
$V_{R} = 50 \text{ V}$		-	-	0.2	
$V_{\rm R} = 50 \text{ V}, \ T_{\rm A} = 150 \text{ °C}$		-	-	100	
Forward voltage	V _F	-	-	1.3	V
<i>I</i> _F = 100 mA					
AC Characteristics			_		
Diode capacitance	CT	-	-	1.5	pF
$V_{R} = 0 V, f = 1 MHz$					
Reverse recovery time	t _{rr}	-	-	6	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA ,					
$R_{\rm L}$ = 100 Ω					

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Test circuit for reverse recovery time



Pulse generator: $t_{\rm p}$ = 100ns, D = 0.05, $t_{\rm r}$ = 0.6ns, $R_{\rm i}$ = 50 Ω

Oscillograph: $R = 50\Omega$, $t_r = 0.35$ ns, $C \le 1$ pF



Reverse current $I_{R} = f(T_{A})$

 $V_{\rm R}$ = Parameter



Forward Voltage $V_{\rm F} = f(T_{\rm A})$

 $I_{\rm F}$ = Parameter



Forward current $I_{\rm F} = f (V_{\rm F})$

 $T_{\rm A} = 25^{\circ}{\rm C}$



Peak forward current $I_{FM} = f(t_p)$ $T_A = 25^{\circ}C$





Forward current $I_{\rm F} = f(T_{\rm S})$

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